

EH25 25 Series -RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm Ceramic SMD HCMOS/TTL High Frequency Oscillator Frequency Tolerance/Stability ±25ppm Maximum

T TS -49.152M

Nominal Frequency 49.152MHz

Pin 1 Connection Tri-State (High Impedance)

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**Operating Temperature Rang** 0°C to +70°C

	Duty Cycle
je į	50 ±5(%)

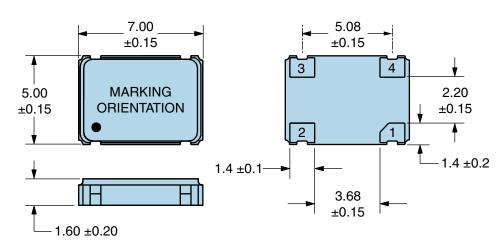
EL	ECTR	SPEC	<b>IFICAT</b>	IONS

49.152MHz	
±25ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)	
±5ppm/year Maximum	
0°C to +70°C	
5.0Vdc ±10%	
50mA Maximum (No Load)	
2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)	
0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)	
6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)	
50 $\pm$ 5(%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)	
10TTL Load or 50pF HCMOS Load Maximum	
CMOS	
Tri-State (High Impedance)	
+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.	
±250pSec Maximum, ±100pSec Typical	
±50pSec Maximum, ±30pSec Typical	
10mSec Maximum	
-55°C to +125°C	

## **ENVIRONMENTAL & MECHANICAL SPECIFICATIONS**

IIL-STD-883, Method 3015, Class 1, HBM: 1500V	
MIL-STD-883, Method 1014, Condition A	
_94-V0	
L-STD-883, Method 1014, Condition C	
L-STD-883, Method 2002, Condition B	
MIL-STD-883, Method 1004	
J-STD-020, MSL 1	
MIL-STD-202, Method 210, Condition K	
MIL-STD-202, Method 215	
MIL-STD-883, Method 2003	
MIL-STD-883, Method 1010, Condition B	
MIL-STD-883, Method 2007, Condition A	

## **MECHANICAL DIMENSIONS (all dimensions in millimeters)**

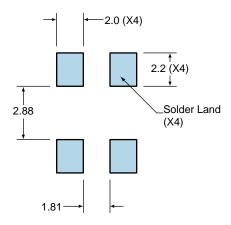


		 <b>EK</b> TION

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1	Tri-State
2	Ground
3	Output
4	Supply Voltage
LINE	MARKING
1	ECLIPTEK
2	49.152M
3	XXXXXX

### Suggested Solder Pad Layout

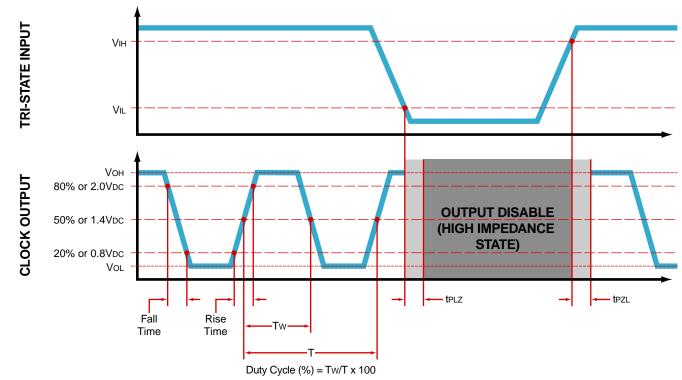
All Dimensions in Millimeters



All Tolerances are ±0.1



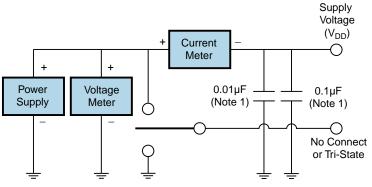
#### **OUTPUT WAVEFORM & TIMING DIAGRAM**

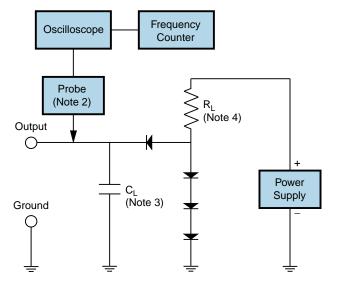


### Test Circuit for TTL Output

Output Load Drive Capability	R <sub>L</sub> Value (Ohms)	C <sub>L</sub> Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3







Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth

(>300MHz) passive probe is recommended.

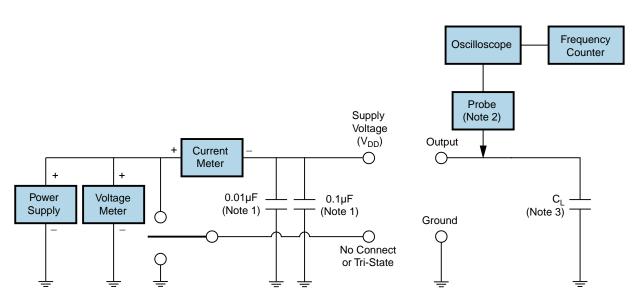
Note 3: Capacitance value  $C_{\text{L}}$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value RL is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



### **Test Circuit for CMOS Output**



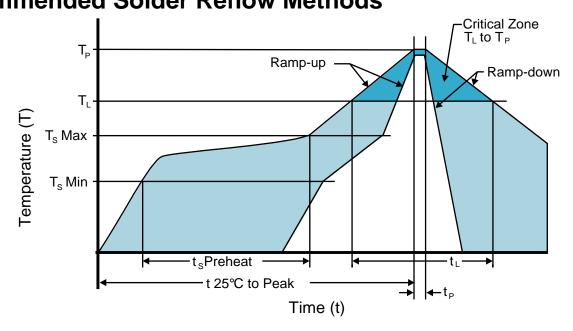
Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_1$  includes sum of all probe and fixture capacitance.



# EH2525TTS-49.152M Recommended Solder Reflow Methods



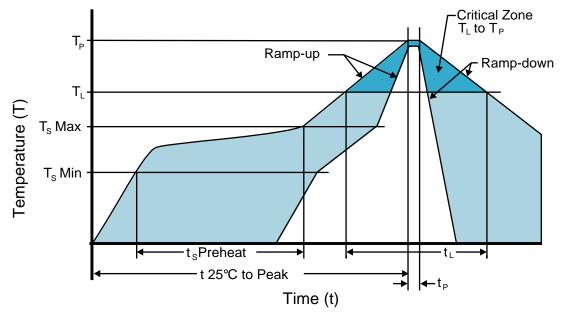
## **High Temperature Infrared/Convection**

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



# **Recommended Solder Reflow Methods**

EH2525TTS-49.152M



## Low Temperature Infrared/Convection 240°C

$T_s$ MAX to $T_L$ (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t <sub>p</sub> )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

## High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)